



DMN3020LK3

30V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)}$	I_D $T_A = 25^\circ C$
30V	20mΩ @ $V_{GS} = 10V$	16.7A
	34mΩ @ $V_{GS} = 4.5V$	12.6A

Description and Applications

This new generation MOSFET has been designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

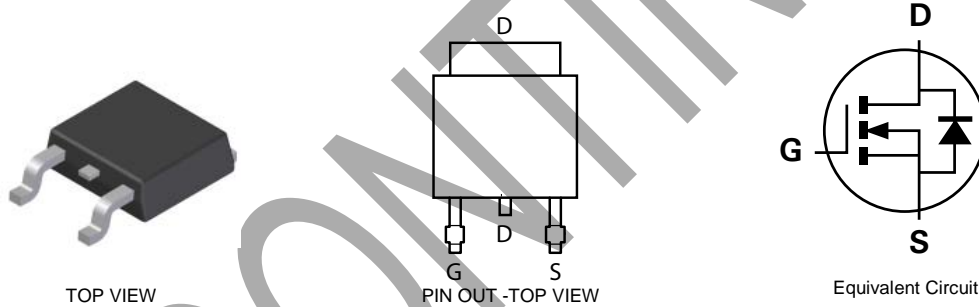
- Backlighting
- DC-DC Converters
- Power management functions

Features and Benefits

- Low on-resistance
- Fast switching speed
- "Green" Component and RoHS compliant

Mechanical Data

- Case: TO252-3L
- Case Material: Molded Plastic "Green" Molding Compound, UL Flammability Classification Rating 94V-0 (Note 1)
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208 @3
- Marking Information: See Below
- Ordering Information: See Below
- Weight: 0.33 grams (approximate)

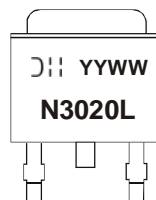


Ordering Information (Note 1)

Product	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
DMN3020LK3-13	N3020L	13	16	2,500

Notes: 1. Diodes, Inc. defines "Green" products as those which are Eu RoHS compliant and contain no halogens or antimony compounds; further information about Diodes Inc.'s "Green" Policy can be found on our website. For packaging details, go to our website.

Marking Information



⌋⌋⌋ = Manufacturer's Marking
 N3020L = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last two digits of year (ex: 09 = 2009)
 WW = Week (01-52)

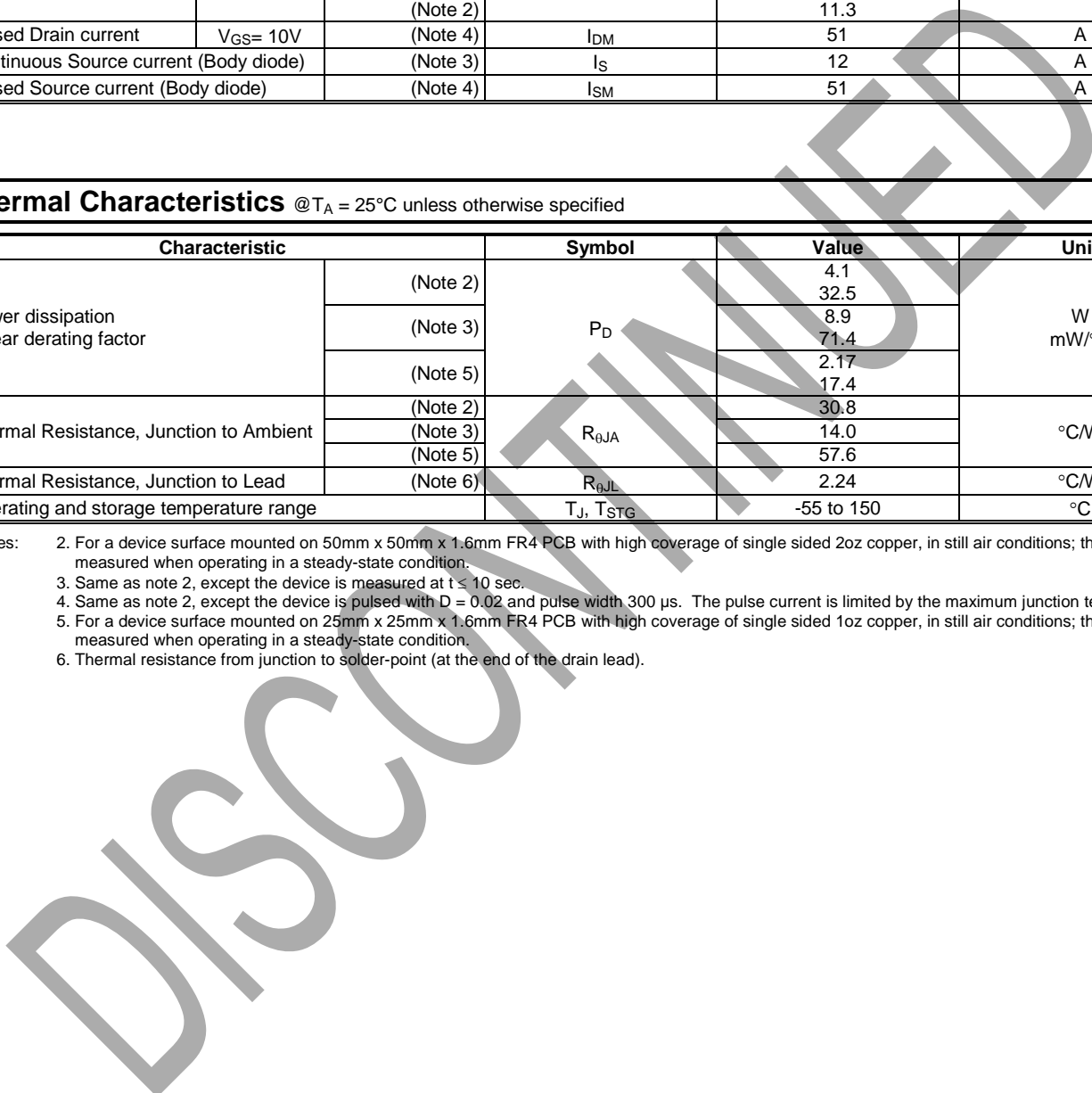
Maximum Ratings @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit	
Drain-Source voltage		V_{DSS}	30	V	
Gate-Source voltage		V_{GS}	± 20	V	
Continuous Drain current	$V_{GS} = 10\text{V}$	(Note 3)	16.7	A	
		$T_A = 70^\circ\text{C}$ (Note 3)	13.3		
		(Note 2)	11.3		
Pulsed Drain current	$V_{GS} = 10\text{V}$	(Note 4)	I_{DM}	51	A
Continuous Source current (Body diode)		(Note 3)	I_S	12	A
Pulsed Source current (Body diode)		(Note 4)	I_{SM}	51	A

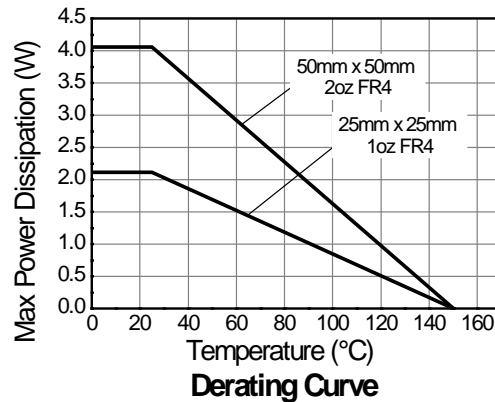
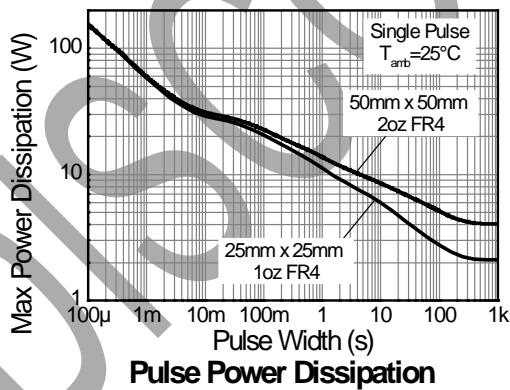
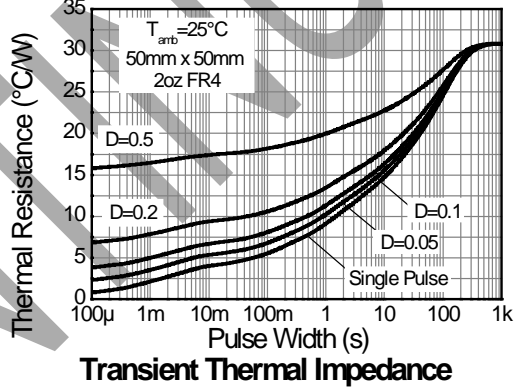
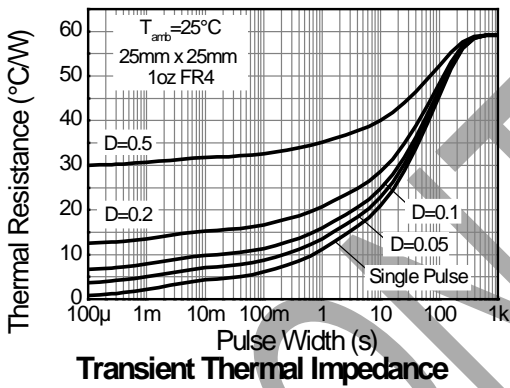
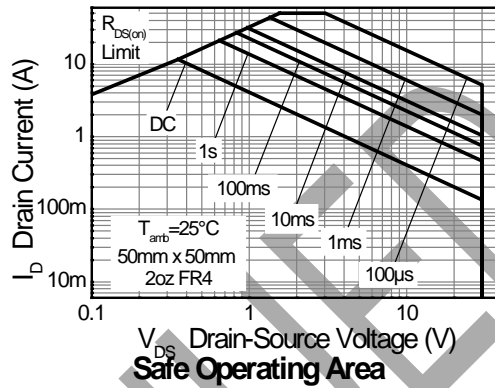
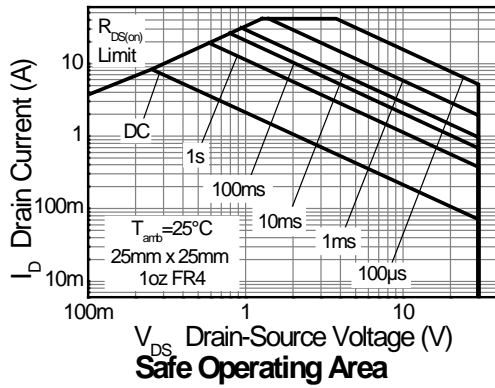
Thermal Characteristics @ $T_A = 25^\circ\text{C}$ unless otherwise specified

Characteristic		Symbol	Value	Unit
Power dissipation Linear derating factor	(Note 2)	P_D	4.1	W mW/ $^\circ\text{C}$
	(Note 3)		32.5	
	(Note 5)		8.9	
	(Note 5)		71.4	
	(Note 5)		2.17	
Thermal Resistance, Junction to Ambient	(Note 2)	$R_{\theta JA}$	17.4	$^\circ\text{C/W}$
	(Note 3)		30.8	
	(Note 5)		14.0	
Thermal Resistance, Junction to Lead	(Note 6)	$R_{\theta JL}$	57.6	$^\circ\text{C/W}$
Operating and storage temperature range		T_J, T_{STG}	-55 to 150	$^\circ\text{C}$

- Notes:
2. For a device surface mounted on 50mm x 50mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 3. Same as note 2, except the device is measured at $t \leq 10$ sec.
 4. Same as note 2, except the device is pulsed with $D = 0.02$ and pulse width 300 μs . The pulse current is limited by the maximum junction temperature.
 5. For a device surface mounted on 25mm x 25mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Thermal resistance from junction to solder-point (at the end of the drain lead).



Thermal Characteristics



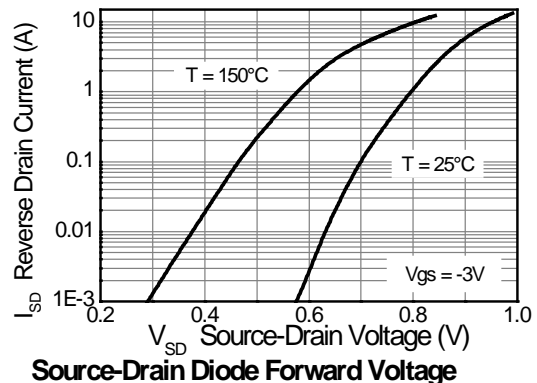
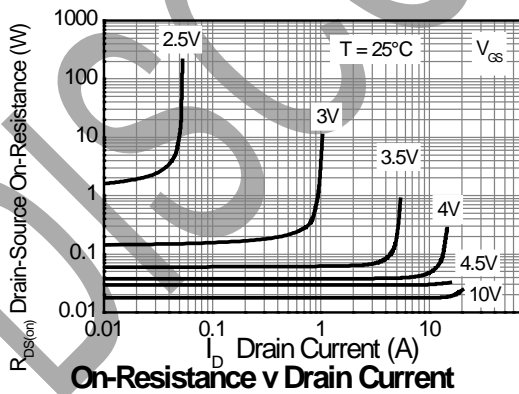
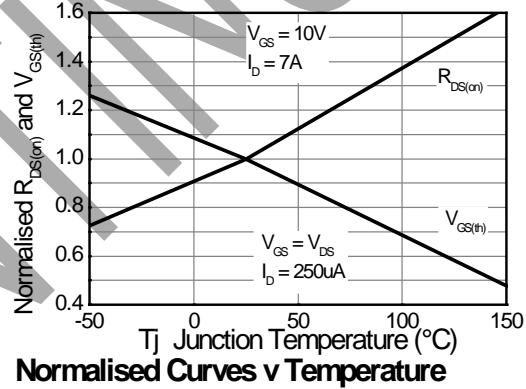
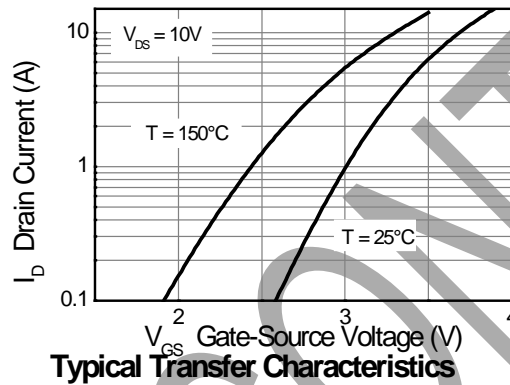
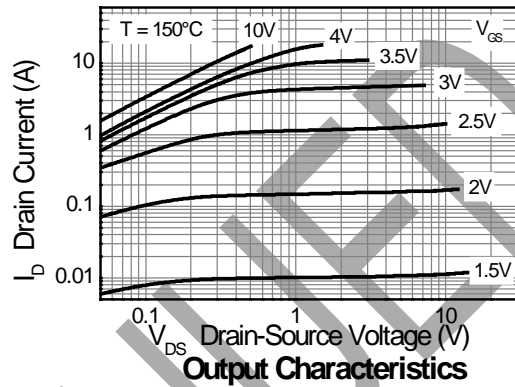
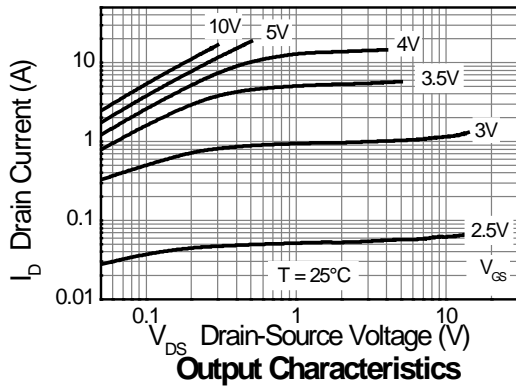
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	30	—	—	V	I _D = 250μA, V _{GS} = 0V
Zero Gate Voltage Drain Current	I _{DSS}	—	—	0.5	μA	V _{DS} = 30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±100	nA	V _{GS} = ±20V, V _{DS} = 0V
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(th)}	1.0	—	3.0	V	I _D = 250μA, V _{DS} = V _{GS}
Static Drain-Source On-Resistance (Note 7)	R _{DS(on)}	—	—	0.020	—	V _{GS} = 10V, I _D = 7.0A
				0.034		V _{GS} = 4.5V, I _D = 6.0A
Forward Transconductance (Notes 7 & 8)	g _{fs}	—	16.5	—	S	V _{DS} = 15V, I _D = 7.1A
Diode Forward Voltage (Note 7)	V _{SD}	—	0.82	1.2	V	I _S = 1.7A, V _{GS} = 0V
Reverse recovery time (Note 8)	t _{rr}	—	12	—	ns	I _S = 2.2A, di/dt = 100A/μs
Reverse recovery charge (Note 8)	Q _{rr}	—	4.8	—	nC	
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	C _{iss}	—	608	—	pF	V _{DS} = 15V, V _{GS} = 0V f = 1MHz
Output Capacitance	C _{oss}	—	132	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	71	—	pF	
Total Gate Charge	Q _g	—	6.3	—	nC	V _{DS} = 15V, V _{GS} = 4.5V I _D = 7A
Total Gate Charge	Q _g	—	12.9	—	nC	V _{DS} = 15V, V _{GS} = 10V I _D = 7A
Gate-Source Charge	Q _{gs}	—	2.5	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.5	—	nC	
Turn-On Delay Time (Note 9)	t _{D(on)}	—	2.9	—	ns	V _{DD} = 15V, V _{GS} = 10V I _D = 1A, R _G ≅ 6.0Ω
Turn-On Rise Time (Note 9)	t _r	—	3.3	—	ns	
Turn-Off Delay Time (Note 9)	t _{D(off)}	—	16	—	ns	
Turn-Off Fall Time (Note 9)	t _f	—	8	—	ns	

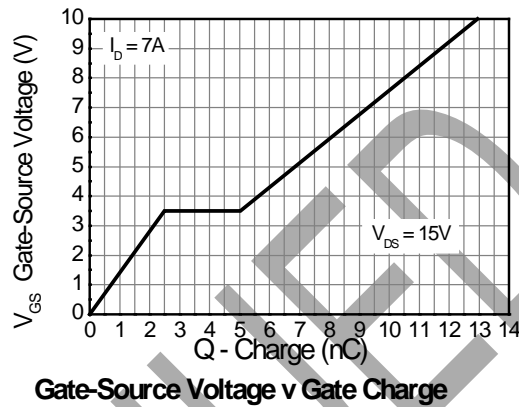
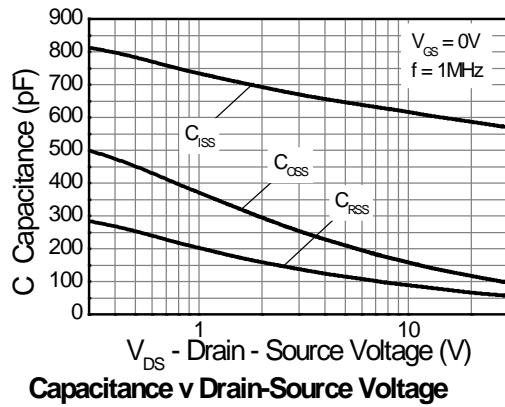
- Notes:
7. Measured under pulsed conditions. Pulse width ≤ 300μs; duty cycle ≤ 2%
 8. For design aid only, not subject to production testing.
 9. Switching characteristics are independent of operating junction temperatures.

DISCONTINUED

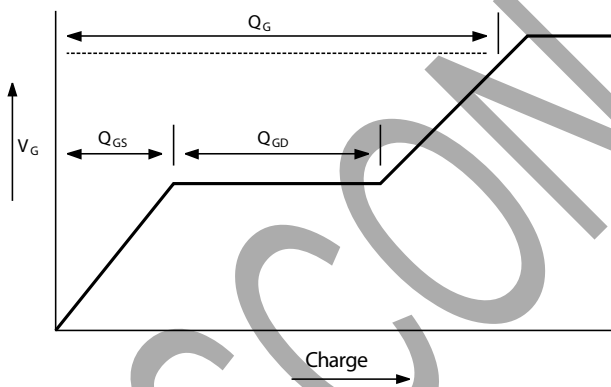
Typical Characteristics



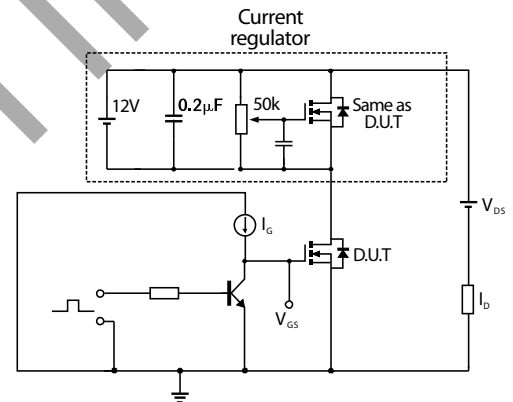
Typical Characteristics - continued



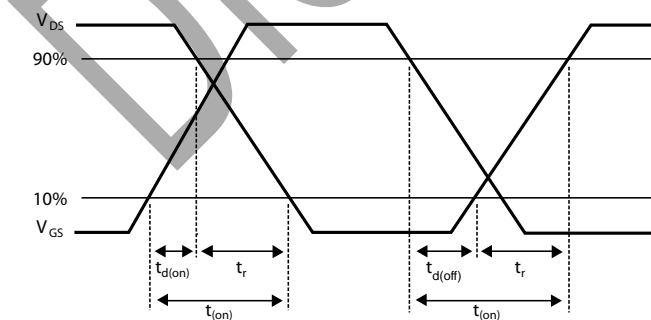
Test Circuits



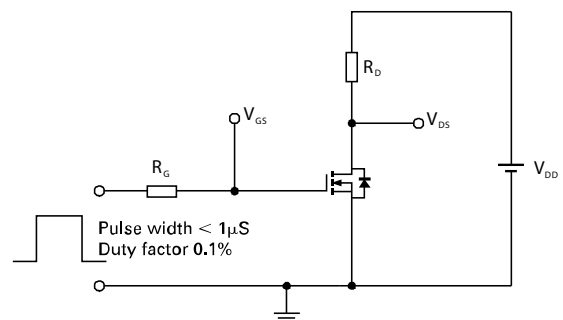
Basic gate charge waveform



Gate charge test circuit

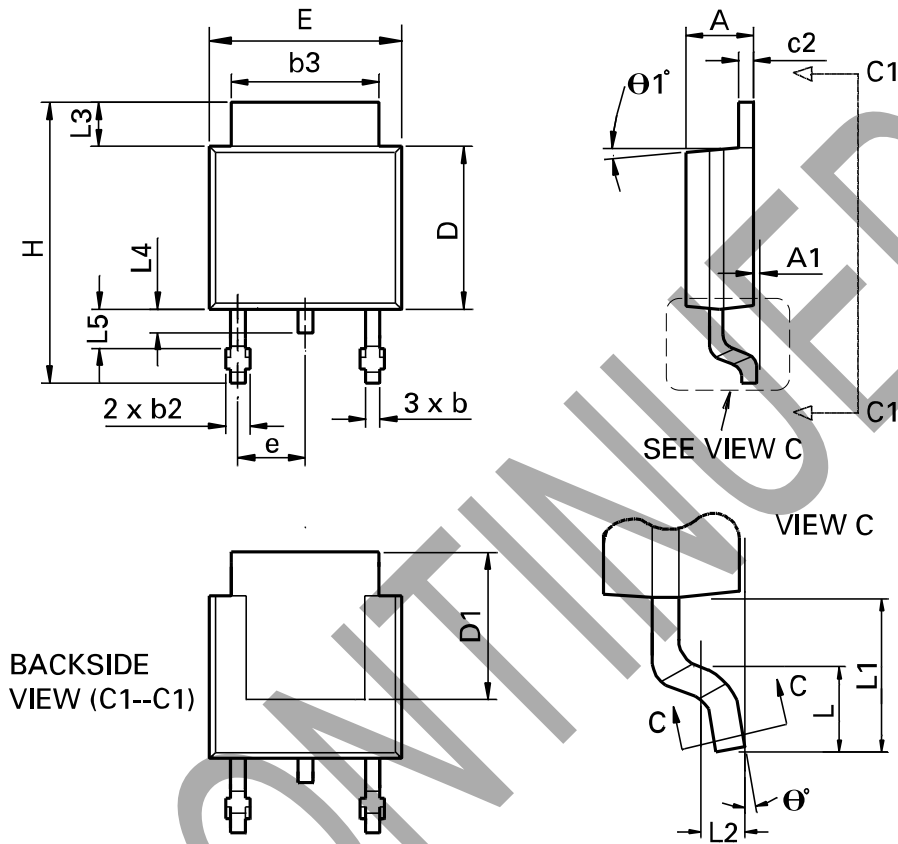


Switching time waveforms



Switching time test circuit

Package Outline Dimensions



DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min	Max	Min	Max		Min	Max	Min	Max
A	0.086	0.094	2.18	2.39	e	0.090 BSC		2.29 BSC	
A1	-	0.005	-	0.127	H	0.370	0.410	9.40	10.41
b	0.020	0.035	0.508	0.89	L	0.055	0.070	1.40	1.78
b2	0.030	0.045	0.762	1.14	L1	0.108 REF		2.74 REF	
b3	0.205	0.215	5.21	5.46	L2	0.020 BSC		0.508 BSC	
c	0.018	0.024	0.457	0.61	L3	0.035	0.065	0.89	1.65
c2	0.018	0.023	0.457	0.584	L4	0.025	0.040	0.635	1.016
D	0.213	0.245	5.41	6.22	L5	0.045	0.060	1.14	1.52
D1	0.205	-	5.21	-	•1°	0°	10°	0°	10°
E	0.250	0.265	6.35	6.73	•°	0°	15°	0°	15°
E1	0.170	-	4.32	-	-	-	-	-	-

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